

**AMENDMENTS TO THE SPECIFICATION**

IN THE SPECIFICATION:

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Immediately above the "BACKGROUND OF THE INVENTION", please insert the following new section:

This Nonprovisional application claims priority under 35 U.S.C. § 119(a) on Patent Application No(s). 2002-327148 and 2003-206544 filed in Japan on November 11, 2002 and August 7, 2003, respectively, the entire contents of which are hereby incorporated by reference.

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Please replace the paragraphs commencing at line 22 through line 30 with the following amended paragraphs:

As shown in Fig. 10, the semiconductor laser device of the fifth embodiment has a planar sapphire substrate 41. A GaN buffer layer 42 is provided to cover the top surface of sapphire substrate 41. On GaN buffer layer 42, ~~[[an]]~~ n-type GaN contact ~~layer 43~~ ~~(44)~~ is layers 43 and 44 are provided. In n-type GaN contact layer 43, a cut 43a is made to extend in one direction. Cut 43a partially exposes GaN buffer layer 42. Cut 43a extends to reach a protrusion 43b of n-type GaN contact layer 43.

. N-type GaN contact ~~layer 43 has its~~layers 43 and 44 have top  
surface 43c provided with n-electrodes 52 and 53 separated from  
each other by cut 43a.